

International Application No.: PCT/JP03/07055
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IN THE ABSTRACT:

Please replace the Abstract of the Disclosure originally filed with the above-identified patent application with the following Abstract:

ABSTRACT OF THE DISCLOSURE

A semiconductor device having excellent crystallinity and excellent electric characteristics ~~is provided, wherein the semiconductor device~~ includes a ZnO thin film having excellent surface smoothness. ZnO-based thin films (an n-type contact layer-6, an n-type clad layer-7, an active layer-8, a p-type clad layer-9, and a p-type contact layer-10) ~~primarily containing~~including ZnO are formed sequentially by an ECR sputtering method or ~~the like~~other suitable method on a zinc-polar surface ~~1a~~ of a ZnO substrate-1. A transparent electrode 3 and a p-side electrode 4 are formed by an evaporation method or ~~the like~~other suitable method on a surface of the p-type contact layer-10, and an n-side electrode 5 is formed on an oxygen-polar surface ~~1b~~ of the ZnO substrate-1.